
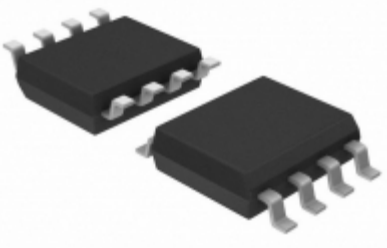
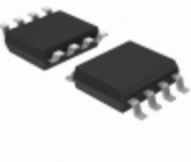


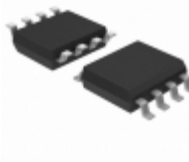
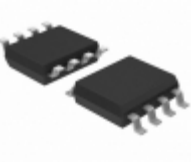



	<h2>SI4196DY-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI4196DY-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 8A 8SOIC</p> <p>Datenblätter:  SI4196DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 17490 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4196DY-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 8A 8SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	17490 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2W (Ta), 4.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Tc)
Rds On (Max) @ Id, Vgs	27 mOhm @ 8A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	22nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	830pF @ 10V
Verpackung	Tape & Reel (TR)



















































SI4196DY-T1-GE3 ist neu im Original, Suche SI4196DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4196DY-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI4196DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4196DY-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 8A 8SOIC</p>	 <p>SI4200-BM Energy Micro (Silicon Labs) IC RF TXRX CELLULAR 32-VFQFN</p>	 <p>SI4200-GMR SILICONIX SI4200-GMR SILICONIX</p>	 <p>SI4196DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 8A 8SOIC</p>
 <p>SI4190DY-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 20A 8-SOIC</p>	 <p>SI4200-BMR SILICON SI4200-BMR SILICON</p>	 <p>SI4200-GM Energy Micro (Silicon Labs) IC RF TXRX CELLULAR 32-VFQFN</p>	 <p>SI4200-EVB Energy Micro (Silicon Labs) BOARD EVAL FOR SI4200</p>

heiße Teile

Mehr

 SI4168DY	 SI4168DY-T1-E3	 SI4168DY-T1-GE3	 SI4168DY-T1-GE3	 SI4170DY-T1-GE3
 SI4170DY-T1-GE3	 SI4172DY	 SI4172DY-T1-E3	 SI4172DY-T1-GE3	 SI4172DY-T1-GE3
 SI4174DY	 SI4174DY-T1-E3	 SI4174DY-T1-GE3	 SI4174DY-T1-GE3	 SI4176DY-T1-GE3
 SI4176DY-T1-GE3	 SI4178DY	 SI4178DY-T1-E3	 SI4178DY-T1-E3	 SI4178DY-T1-GE3
 SI4178DY-T1-GE3	 SI4186DY-T1-E3	 SI4188DY-T1-E3	 SI4190ADY	 SI4196DY-T1-GE3
 SI4200-BM	 SI4200-BMR	 SI4200-GM	 SI4200-GMR	 SI4200BM
 SI4200DB-BMR	 SI4200DY-T1-E3	 SI4201-BMR	 SI4201-GMR	 SI4202DY
 SI4205-BM	 SI4205-BMR	 SI4206-BM	 SI4206-BMR	 SI4208-A-GMR
 SI4208GM	 SI4209-A-GMR	 SI4210-C-GMR	 SI4210-D-GMR	 SI4210-GM
 SI4210DY-T1-E3	 SI4210DY-T1-GE3	 SI4210DY-T1-GE3	 SI4210GM	 SI4214DDY

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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